

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (currently amended): A semiconductor device, comprising:

a source region formed of a semiconductor;

a drain region formed of a semiconductor of the same conductive type as that of said source region;

a channel region formed of a semiconductor between said source region and said drain region;

a gate insulating film provided on said channel region; and

a gate electrode provided on said gate insulating film and formed with a P-N junction including a P-type semiconductor region and an N-type semiconductor region,

wherein said P-type semiconductor region and said N-type semiconductor region of said P-N junction of said gate electrode are electrically insulated on all sides,

wherein said gate electrode includes a first gate portion provided above said channel region and a second gate portion provided ~~above a region which is not~~ in the semiconductor device overlying outside of a region which consists of said channel region, said source region ~~[[or]]~~ and said drain region, and said second gate portion includes said P-N junction.

2. (original): The semiconductor device according to claim 1,  
wherein silicide is not formed on said P-N junction of said gate electrode.
3. (original): The semiconductor device according to claim 1,  
wherein said P-N junction of said gate electrode is covered with an insulating material.
4. (original): The semiconductor device according to claim 3,  
wherein silicide is formed on a part of said gate electrode which is not covered with said  
insulating material.
5. (canceled)
6. (previously presented): The semiconductor device according to claim 1, further  
comprising;  
a body region formed of a semiconductor under said channel region;  
a buried insulating film provided under said body region, said source region, and said drain  
region; and  
a semiconductor substrate region provided under said buried insulating film.
7. (original): The semiconductor device according to claim 1,  
wherein silicide is formed on surfaces of said source region and said drain region.

8. (original): The semiconductor device according to claim 6, further comprising;  
a body contact region formed within said body region and having a higher impurity concentration than said body region.

9. (original): The semiconductor device according to claim 8,  
wherein said body contact region is formed in a region outside said second gate portion.

10-12. (canceled)